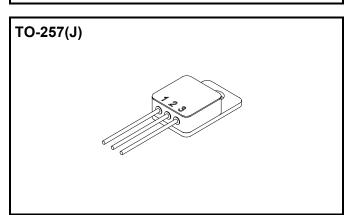


FEATURES:

- PIV: 100 Volts
- Average Output Current 25 Amps
- Low Reverse Leakage Current
- Low Forward Voltage Drop
- Guard Ring for Overvoltage Protection
- Isolated Hermetically Sealed Package
- Custom Lead Forming Available
- Eutectic Die Attach
- Ultrasonic Aluminum Wire Bonds
- 175°C Operating Junction Temperature
- TX, TXV, and Space Level Screening Available. Consult Factory.

SSR2010J Series

20 AMPS 100 VOLTS SCHOTTKY RECTIFER



MAXIMUM RATINGS <u>1/</u>	Symbol	Value	Unit
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	Volts
Average Rectified Forward Current $\frac{2}{}$ (Resistive Load, 60 Hz, Sine Wave, T _A = 25°C)	lo	20	Amps
Peak Surge Current $\frac{2}{}$ (8.3 ms Pulse, Half Sine Wave, Superimposed on Io, Allow Junction to reach equilibrium between pulses, $T_A = 25^{\circ}C$)	I _{FSM}	300	Amps
Operating and Storage Temperature	T _{OP} & T _{stg}	-65 to +175	Ĵ
Maximum Thermal Resistance ^{2/} (Junction to Case)	R _{θJC}	1.0	°C/W

Available in the Following Configurations:

Rectifier:SSR2010J, SSR2010JDB, and SSR2010JUBCommon Cathode Centertap:SSR2010CTJ, SSR2010CTJDB, and SSR2010CTJUB (See Data Sheet RS0073)Common Anode Centertap:SSR2010CAJ, SSR2010CAJDB, and SSR2010CAJUB (See Data Sheet RS0073)

NOTE:

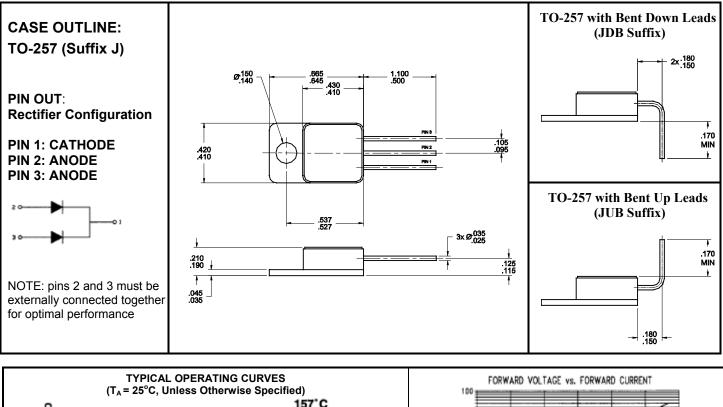
- 1/ at room temperature, unless otherwise specified
- 2/ pins 2 and 3 connected together

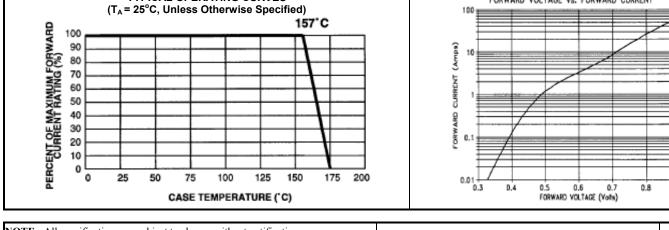
NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: RS0087G	DOC
Seb s for these devices should be reviewed by SSB1 prior to release.	1	

SSR2010J Series

Solid State Devices, Inc. 14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

ELECTRICAL CHARACTERISTICS (per leg)		Symbol	Max	Unit
Instantaneous Forward Voltage Drop (T _A = 25 $^{\circ}$ C, 300 μ s Pulse)	I _F = 10 A I _F = 15 A I _F = 20 A	V _{F1} V _{F2} V _{F3}	0.8 0.97 1.00	Volts
Instantaneous Forward Voltage Drop ($T_A = -55^{\circ}C$, 300 µs Pulse)	I _F = 10 A	V _{F4}	0.93	Volts
Reverse Leakage Current (Rated V _R , 300 μ s pulse minimum)	T _A = 25 [°] C T _C = 100 [°] C	I _{R1} I _{R2}	200 10	μA mA
Junction Capacitance ($V_R = 10 \text{ Vdc}, T_A = 25 \text{ C}, f = 1 \text{MHz}$)		Сյ	800	pf





NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RS0087G

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